



# Flash Programmable Capacitor Tuning Array Die for Crystal Oscillator(XO)

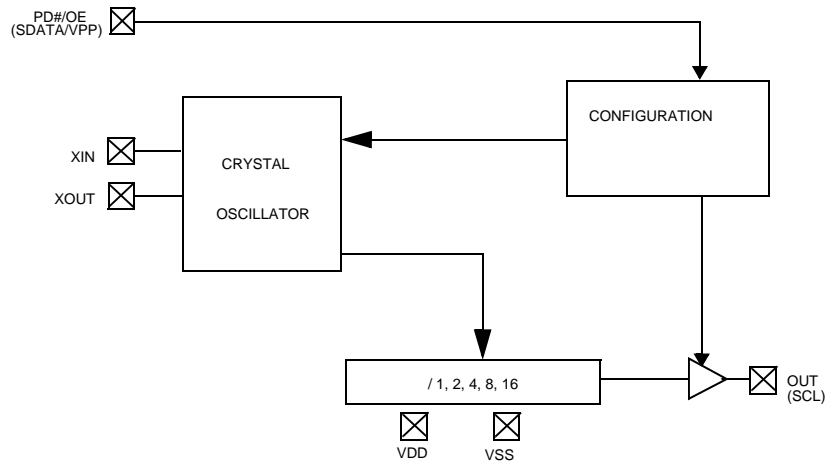
## Features

- Flash-programmable capacitor tuning array for low ppm initial frequency clock output
- Low clock output jitter
  - 4 ps typ. RMS period jitter
  - ±30 ps typ. peak-to-peak period jitter
- Flash-programmable dividers
- Two-pin programming interface
- On-chip oscillator runs from 10–48-MHz crystal
- Five selectable post-divide options, using reference oscillator output
- Programmable asynchronous or synchronous OE and PWR\_DWN modes
- 2.7V to 3.6V operation
- Controlled rise and fall times and output slew rate

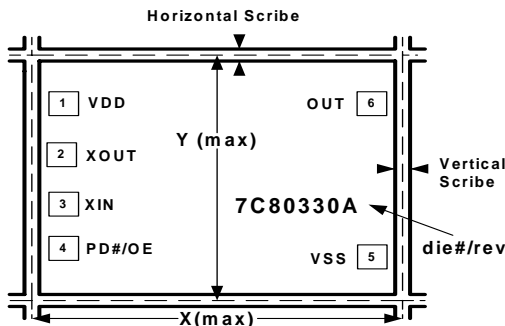
## Benefits

- Enables fine-tuning of output clock frequency by adjusting  $C_{Load}$  of the crystal
- Allows multiple programming opportunities to correct errors, and control excess inventory
- Enables programming of output frequency after packaging
- PPM clock output error can be adjusted in package
- Provides flexibility in output configurations and testing
- Enables low-power operation or output enable function
- Provides flexibility for system applications through selectable instantaneous or synchronous change in outputs
- Enables encapsulation in small-size, surface-mount packages

## Block Diagram



## Die Pad Description



### Notes:

- X(max): 980 μm, Y(max): 988 μm
- Scribe: X = 70 μm, Y = 86 μm
- Bond pad opening: 85 μm x 85 μm
- Pad pitch: 175 μm (min.)
- Wafer thickness: 11 mils (Typ.)

**Die Pad Summary** (Pad coordinates are referenced from the center of the die (X = 0, Y = 0))

Name	PadNumber	Description	X coordinate (μm)	Y coordinate (μm)
VDD	1	Voltage Supply	-360.8	353.7
XOUT	2	Oscillator Drain	-360.8	134.1
XIN	3	Oscillator Gate	-360.8	-42.6
PD#/OE	4	Programmable power-down or output enable pin	-360.8	-275.9
VPP		High voltage for programming NV memory		
SDATA		Serial data pin used for programming in test mode		
OUT	6	Clock output	360.0	353.7
SCL		Serial clock for programming in test mode		
VSS	5	Ground	360.0	-354.5

**Absolute Maximum Conditions**

(Above which the useful life may be impaired.  
For user guidelines, not tested.)

Supply Voltage ( $V_{DD}$ ) ..... -0.5 to +7.0V  
DC Input Voltage..... -0.5V to  $V_{DD} + 0.5$

Output Short Circuit Current.....  $\pm 50$  mA  
Storage Temperature (Non-condensing) .... -55°C to +125°C  
Junction Temperature ..... -40°C to +125°C  
Data Retention @  $T_j = 125^\circ\text{C}$ ..... > 10 years  
ESD (Human Body Model) MIL-STD-883..... > 2000V

**Crystal Specifications<sup>[1]</sup>**

Parameter	Description	Comments	Min.	Typ.	Max.	Unit
$F_{NOM}$	Nominal crystal frequency	Fundamental mode, AT cut	10	-	48	MHz
$R_1$	Equivalent series resistance (ESR)	Fundamental mode	-	-	40	$\Omega$
$R_3/R_1$	Ratio of third overtone mode ESR to fundamental mode ESR	Ratio used because typical $R_1$ values are much less than the maximum spec	4.5	-	-	-
$C_0$	Crystal shunt capacitance		-	-	5	pF
$C_1$	Crystal motional capacitance		2	-	-	fF

**Operating Conditions**

Parameter	Description	Min.	Typ.	Max.	Unit
$V_{DD}$	Operating Voltage	2.7	-	3.6	V
$T_J$	Junction Temperature	-40	-	125	$^\circ\text{C}$
$C_{XIN}$	Capacitance XIN, all tuning caps OFF	-	10	-	pF
$C_{XOUT}$	Capacitance XOUT, all tuning caps OFF	-	10	-	pF
$C_L$	All tuning Caps OFF	4	5	6	pF
	All tuning Caps ON	9.2	10	11.4	pF
$C_{OUT}$	Output Load Capacitance	-	-	15	pF
$t_{RAMP}$	Power-up time for $V_{DD}$ to reach minimum specified voltage (power ramps must be monotonic)	0.05	-	500	ms
$T_S$	Start up time, 90% $V_{DD}$ to valid frequency on output	-	-	10	ms

**DC Electrical Specifications**  $T_J = -40$  to  $125^\circ\text{C}$  over the operating range

Parameter	Description	Condition	Min.	Typ.	Max.	Unit
$V_{IL}$	Input Low Voltage	CMOS Levels	-	-	20	% $V_{DD}$
$V_{IH}$	Input High Voltage	CMOS Levels	80	-	-	% $V_{DD}$
$V_{OL}$	Output Low Voltage	$V_{DD} = 2.7\text{V}-3.6\text{V}$ , $I_{OL} = 8$ mA	-	-	0.4	V
$V_{OH}$	Output High Voltage	$V_{DD} = 2.7\text{V}-3.6\text{V}$ , $I_{OL} = -8$ mA	$V_{DD}-0.4$	-	-	V
$I_{IL}$	Input Low Current	Input = $V_{SS}$	-	1	10	$\mu\text{A}$
$I_{IH}$	Input High Current	Input = $V_{DD}$	-	1	10	$\mu\text{A}$
$I_{OZL}$	Output Leakage Current	Output = $V_{SS}$	-	1	10	$\mu\text{A}$
$I_{OZH}$	Output Leakage Current	Output = $V_{DD}$	-	-	50	$\mu\text{A}$
$I_{DD}$	Power Supply Current	No Load, $V_{DD} = 3.3\text{V}$ , 48 MHz	-	-	20	mA
$I_{PD}$	Power Down Current	PD# = 0V	-	-	25	$\mu\text{A}$
$R_{UP}$	Input Pull-up resistor	$V_{IN} = V_{SS}$	1	3	6	M $\Omega$
		$V_{IN} > = 0.8V_{DD}$	80	120	150	k $\Omega$
$R_{DN}$	Output Pull-down resistor	$V_{IN} = 0.5V_{DD}$	500	900	1500	k $\Omega$
$C_{IN}$	Input Pin Capacitance	PD#/OE pin	-	-	7	pF
$R_F$	Crystal Feedback R	XIN = 0	300	-	800	k $\Omega$

**Note:**

1. Not 100% tested.

**AC Electrical Specifications<sup>[1]</sup>** over the operating range, except as noted

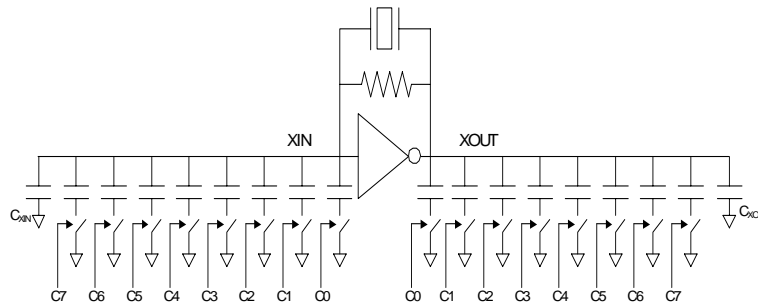
Parameter <sup>[1]</sup>	Description	Condition	Min.	Typ.	Max.	Unit
F <sub>OUT</sub>	Output Frequency		0.625	–	48	MHz
DC	Output Duty Cycle	XTAL Buffered or Divided	45	50	55	%
T <sub>R</sub>	Rise Time	Output Clock Rise Time, Measured from 20% to 80% of V <sub>DD</sub> , C <sub>OUT</sub> = 15 pF.			2.5	ns
T <sub>F</sub>	Fall Time	Output Clock Fall Time, Measured from 80% to 20% of V <sub>DD</sub> , C <sub>OUT</sub> = 15 pF.			2.5	ns
t <sub>PJ1</sub>	RMS Period Jitter	XIN = 10–48 MHz. Measured at V <sub>DD</sub> /2	–	4	15	ps
t <sub>PJ2</sub> <sup>[2]</sup>	Peak-to-peak Period Jitter	XIN = 10–48 MHz. Measured at V <sub>DD</sub> /2	–	30	80	ps
DL	Crystal drive level	48-MHz crystal, C <sub>L</sub> = 7 pF, C <sub>0</sub> = 2 pF, R1 = 10 Ohms, Temp. = 25°C, V <sub>DD</sub> = 3.6V	350–400			μW
–R	Negative Resistance	Measured at 48 MHz, C <sub>L</sub> = 10 pF, C <sub>0</sub> = 5 pF	–	–	–150	Ω
F <sub>DRIFT</sub>	Output Frequency Drift	3.0V ± 10%, 3.3V ± 10% for Temp. = 25°C	–2	–	2	ppm

**Phase Noise, Temp = 25°C, V<sub>DD</sub> = 3.3V,  
F<sub>NOM</sub> = 10MHz, X<sub>CAP</sub> = 7F (Hex)**

Offset	dBc/Hz (Typ)
10 Hz	–90
100 Hz	–115
1 kHz	–130
10 kHz	–140
100 kHz	–140
1 MHz	–140

**Crystal Oscillator Tuning Capacitor Values**

Capacitor Bit	Capacitance (pF) per Side
C <sub>7</sub>	5.000
C <sub>6</sub>	2.500
C <sub>5</sub>	1.250
C <sub>4</sub>	0.625
C <sub>3</sub>	0.313
C <sub>2</sub>	0.156
C <sub>1</sub>	0.078
C <sub>0</sub>	0.039



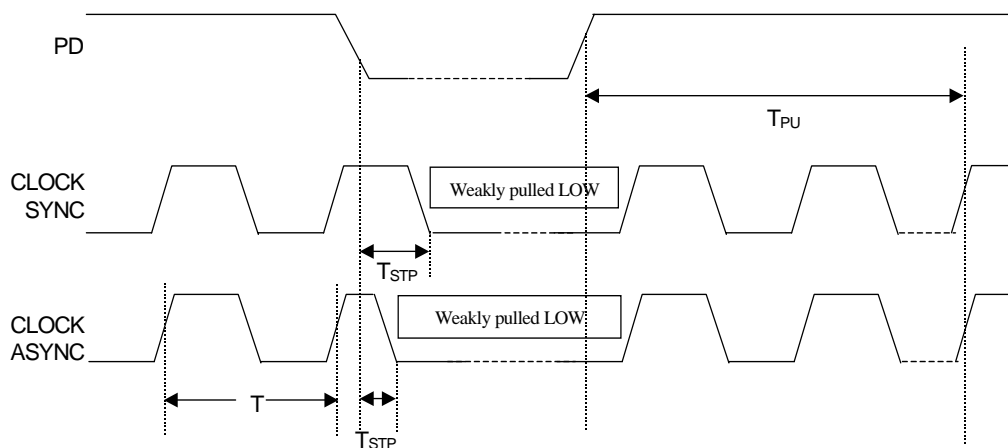
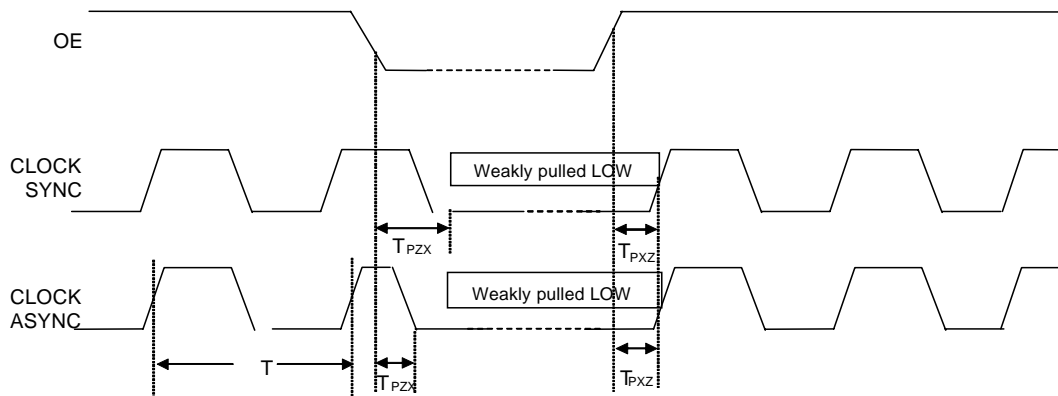
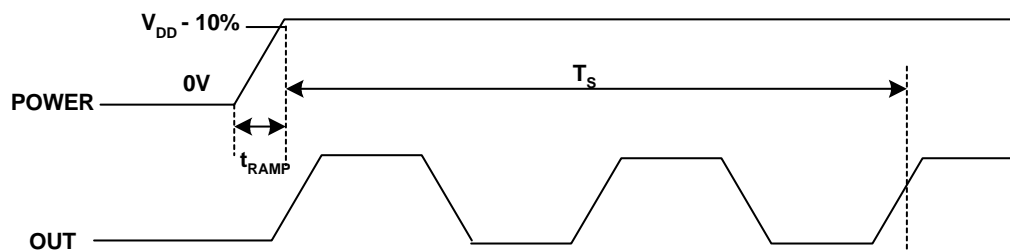
**Figure 1. Programmable Load Capacitance**

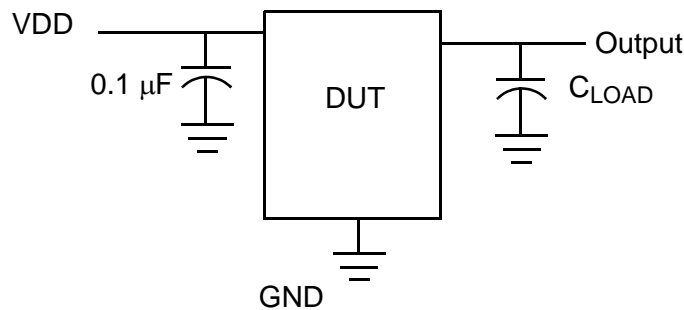
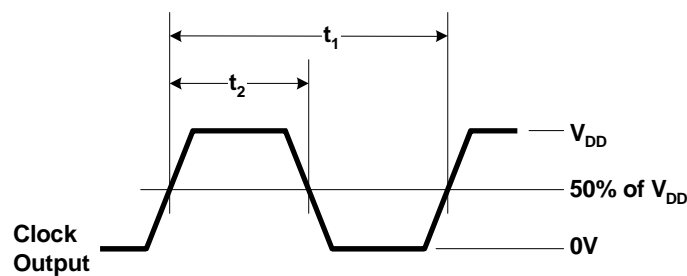
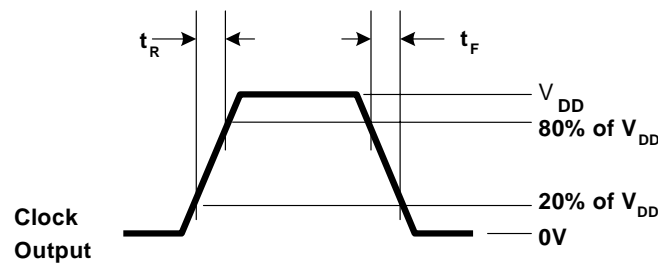
**Notes:**

2. T<sub>PJ2</sub> measured using DTS-2075, # of events set to 10, 000.

**Timing Parameters** over the operating range

Parameter	Description	Min.	Max.	Unit
$T_{STP,SYNC}$	Time from falling edge on PD# to stopped output, synchronous mode, $T=1/F_{out}$		$1.5T + 350$	ns
$T_{STP,ASYNC}$	Time from falling edge on PD# to stopped output, asynchronous mode		350	ns
$T_{PU,SYNC}$	Time from rising edge on PD# to output at valid frequency, synchronous mode, $T = 1/F_{out}$		3	ms
$T_{PU,ASYNC}$	Time from rising edge on PD# to output at valid frequency, asynchronous mode		3	ms
$T_{PZX,SYNC}$	Time from rising edge on OE to running output, synchronous mode, $T=1/F_{out}$		$1.5T + 350$	ns
$T_{PZX,ASYNC}$	Time from rising edge on OE to running output, asynchronous mode		350	ns
$T_{PXZ,SYNC}$	Time from falling edge on OE to high impedance output, synchronous mode, $T = 1/F_{out}$		$1.5T + 350$	ns
$T_{PXZ,ASYNC}$	Time from falling edge on OE to high impedance output, asynchronous mode		350	ns


**Figure 2. Power-down Timing**

**Figure 3. Output Enable Timing**

**Figure 4. VDD Power-up Timing**

**Test and Measurement Set-up**

**Voltage and Timing Definitions**

**Figure 5. Duty Cycle Definition**

**Figure 6.**
**Ordering Information**

Ordering Code	Package Type	Operating Range (TJ)
CY2048WAF <sup>[3]</sup>	Wafer	Industrial, -40 °C to 125°C

**Note:**

3. The product is offered as tested die-on-wafer form. Contact Cypress Sales for additional programming information and support.

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**Document History Page**

Document Title: CY2048WAF Flash Programmable Capacitor Tuning Array Die  
for Crystal Oscillator(XO)  
Document Number: 38-07738

REV.	ECN NO.	Issue Date	Orig. of Change	Description of Change
**	319840	See ECN	RGL	New data sheet
*A	413511	See ECN	RGL	Minor Change: Pls. post in the web